

STPSC2006CW

600 V power Schottky silicon carbide diode

Features

- No or negligible reverse recovery
- Switching behavior independent of temperature
- Particularly suitable in PFC boost diode function

Description

The SiC diode is an ultrahigh performance power Schottky diode. It is manufactured using a silicon carbide substrate. The wide band gap material allows the design of a Schottky diode structure with a 600 V rating. Due to the Schottky construction no recovery is shown at turn-off and ringing patterns are negligible. The minimal capacitive turn-off behavior is independent of temperature.

ST SiC diodes will boost the performance of PFC operations in hard switching conditions.

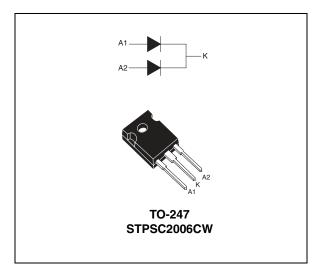


Table 1. Device summary

Symbol	Value
I _{F(AV)}	2 x 10 A
V_{RRM}	600 V
T _{j (max)}	175 °C
Q _{C (typ)}	12 nC

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Table 2. Absolute ratings (limiting values at 25 °C unless otherwise specified, per diode)

Symbol	Parameter			Value	Unit
V_{RRM}	Repetitive peak reverse voltage			600	V
I _{F(RMS)}	Forward rms current			18	Α
1	Average forward current	$T_c = 115 {}^{\circ}\text{C}, \delta = 0.5$	Per diode	10	Α
I _{F(AV)}	Average lorward current	$T_c = 100 ^{\circ}\text{C}, \delta = 0.5$	Per device	20	Α
	Course was atitive forward	$t_p = 10$ ms sinusoidal, $T_c = 25$ °C		40	
I _{FSM}	Surge non repetitive forward current	$t_p = 10 \text{ ms sinusoidal}, T_c = 125 ^{\circ}\text{C}$		32	Α
	Carrent	$t_p = 10 \mu s \text{ square}, T_c = 25 °C$		160	
I _{FRM}	Repetitive peak forward current $\delta = 0.1$, $T_c = 110$ °C, $T_j = 150$ °C		40	Α	
T _{stg}	Storage temperature range			-55 to +175	°C
Tj	Maximum operating junction temperature range			-40 to +175	°C

Table 3. Thermal resistance

Symbol	Parameter	Value	Unit	
В	Junction to case	Per diode	2	°C/W
R _{th(j-c)}	Suricilon to case	Total	1.2	°C/W
R _{th(c)}	Coupling		0.4	°C/W

Table 4. Static electrical characteristics per diode

Symbol	Parameter	Tests conditions		Min.	Тур.	Max.	Unit
I _R ⁽¹⁾	Reverse leakage	T _j = 25 °C	V _R = V _{RRM}	-	30	150	μA
'R`	'R ` current	T _j = 150 °C	VR - VRRM	-	210	1500	μΛ
V _F ⁽²⁾	Forward voltage drop	$T_j = 25 ^{\circ}\text{C}$	I _F = 10 A	-	1.4	1.7	V
VF`'	Forward voltage drop	T _j = 150 °C	IF = IOA	-	1.6	2.1	\ \ \

^{1.} $t_p = 10 \text{ ms}, \delta < 2\%$

To evaluate the conduction losses use the following equation:

$$P = 1.2 \text{ x } I_{F(AV)} + 0.09 \text{ x } I_{F^{2}(RMS)}$$

Table 5. Other parameters per diode

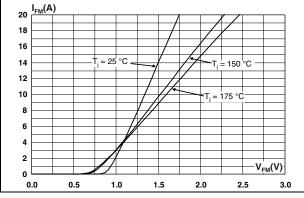
Symbol	Parameter	Test conditions	Тур.	Unit
Q _c	Total capacitive charge	$V_r = 400 \text{ V}, I_F = 10 \text{ A } dI_F/dt = -200 \text{ A/}\mu\text{s}$ $T_j = 150 ^{\circ}\text{C}$	12	nC
С	Total capacitance	$V_r = 0 \text{ V}, T_c = 25 ^{\circ}\text{C}, F = 1 \text{ Mhz}$	650	pF

^{2.} $t_p = 500 \ \mu s, \ \delta < 2\%$

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Figure 1. Forward voltage drop versus forward current (typical values, per diode)

Figure 2. Reverse leakage current versus reverse voltage applied (maximum values, per diode)



1.E+03

1.E+03

1.E+03

1.E+02

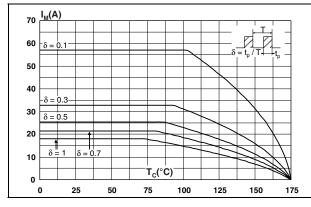
1.E+01

1.E+01

0 50 100 150 200 250 300 350 400 450 500 550 600

Figure 3. Peak forward current versus case temperature (per diode)

Figure 4. Junction capacitance versus reverse voltage applied (typical values, per diode)



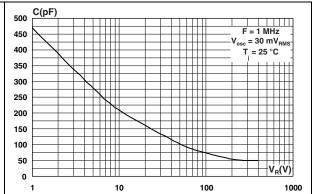
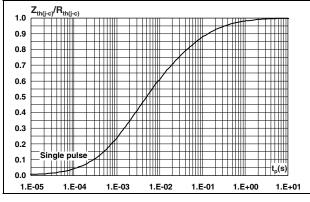
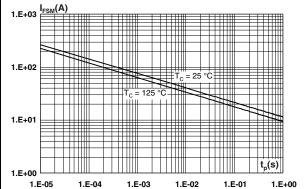


Figure 5. Relative variation of thermal impedance junction to case versus pulse duration

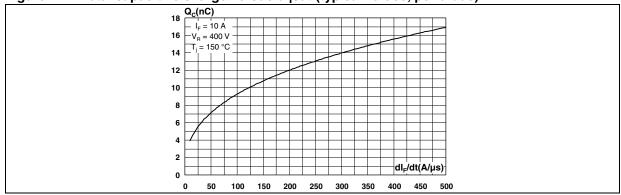
Figure 6. Non-repetitive peak surge forward current versus pulse duration (sinusoidal waveform, per diode)





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Figure 7. Total capacitive charge versus dl_F/dt (typical values, per diode)

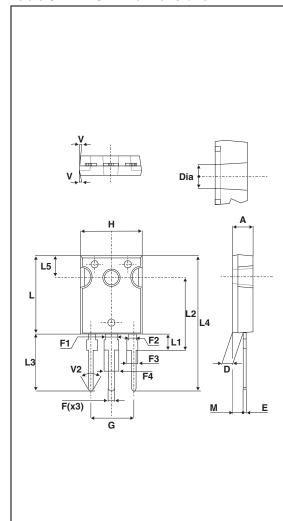


2 Package information

- Epoxy meets UL94, V0
- Cooling method: convection (C)
- Recommended torque value: 0.55 to 1.0 N⋅m

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Table 6. TO-247 dimensions



	Dimensions				
Ref.	Millimeters		Inc	hes	
	Min.	Max.	Min.	Max.	
Α	4.85	5.16	0.191	0.203	
D	2.20	2.60	0.086	0.102	
Е	0.40	0.80	0.015	0.031	
F	1.00	1.40	0.039	0.055	
F1	3.00	typ.	0.118	3 typ.	
F2	2.00	typ.	0.079	9 typ.	
F3	1.90	2.40	0.075	0.094	
F4	3.00 3.40		0.118	0.134	
G	10.90) typ.	0.429 typ.		
Н	15.45	16.03	0.608	0.631	
L	19.85	21.09	0.781	0.830	
L1	3.70	4.30	0.146	0.169	
L2	18.30	19.13	0.720	0.753	
L3	14.20	20.30	0.559	0.799	
L4	34.05	41.38	1.341	1.629	
L5	5.35	6.30	0.211	0.248	
М	2.00	3.00	0.079	0.118	
V	5° typ.		5° typ.		
V2	60°	typ.	60°	typ.	
Dia.	3.55	3.65	0.140	0.144	

Ordering information STPSC2006CW

3 Ordering information

Table 7. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STPSC2006CW	STPSC2006CW	TO-247	4.36 g	30	Tube

4 Revision history

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Table 8. Document revision history

Date	Revision	Changes
01-Mar-2011	1	First issue.

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